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Magnetoelectric Behavior due to Phase Separation and Charge Localized States

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We develop a theory of the magnetoelectric effects which appears in the vicinity of the second order phase transition in the low doped manganites as a result of the long range Coulomb forces. The long range Coulomb interactions is responsible for the formation of the inhomogeneous charged states and determines the characteristic length scales. We derive the phase diagram of the inhomogeneous charged states in the framework of the phenomenological theory of phase transitions. The large value of static dielectric function reduces characteristic value of the Coulomb energy of the inhomogeneous state and makes the appearance of the magnetoelectric effect possible.

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The importance of the inhomogeneous phase segregated states in explanation of the anomalous transport and magnetic properties in manganites [1–6] and in high temperature superconductors [7–9] is widely discussed. In doped manganites the complex interactions between different degrees of freedom lead to unusual magnetic and transport properties. Moreover it was suggested[10] that spiral magnetic order observed in un-doped manganites ReMnO$_3$ may lead to multiferroic behaviour. It was also discussed [11] that the charge ordering in magnetic systems may cause the magnetoelectric effect. Here we propose that the magnetoelectric effect may appear not due to charge ordering but due to charge segregation, which appears near Coulomb frustrated second order phase transition. In this paper we discuss the tendency and conditions of the formation of inhomogeneous states with the spacial charge localization and the phase separation within the phenomenological theory and clarify the role of the Coulomb interaction in this phenomenon. We demonstrate the possibility of magnetoelectric behavior in the low doped manganites and clarify the role of the Janh-Teller interaction.

The problem of Coulomb-frustrated phase separation in different charged systems is the subject of ongoing discussion [3–9, 12–17]. Numerous studies have focused on first-order phase transitions where the charge density is coupled linearly to the order parameter (as an external field) [14, 15] or to the square of the order parameter (local temperature) [16]. However, the Coulomb interaction has mostly been discussed on the qualitative level or as a factor of minor importance [17], rather then analyzing the problem in general. We accurately analyze the total energy of the system and treat Coulomb interaction exactly because it is the key factor which determines the characteristics of inhomogeneous states. The idea of phase segregation and inhomogeneous charge distribution in manganites was successfully applied for the description of the magnetoresistive effect in the limit of the percolating charged regions [2–6]. In this paper we emphasize the possibility of magnetocapacitance effect due to polarization of the non-percolated nano-regions in external electric field in the inhomogeneous state in the low-doped systems.

The phenomenological approach to the theory of Coulomb frustrated phase transition emphasize that the properties the system are universal and are determined by the closeness to the phase transition point and by the dependence of the critical temperature of the phase transition on doping. This approach is essentially independent on other properties of the system. Therefore, the results demonstrate that the properties of the inhomogeneous states are determined by the proximity to the phase transition and the strength of the Coulomb interaction interactions but are independent on other microscopic interactions in manganites. Our estimates show that the Coulomb energy in the charged separated states is relatively small.

We consider a doped system in the vicinity of a second order phase transition. We assume that the free carrier density ρ is proportional to the dopant concentration $x = \rho/\rho_0$, where $\rho_0 = e/a^3$ characteristic carrier density, e is elementary charge, and a is the lattice parameter. The thermodynamic potential $\Phi = \int \phi(\eta,\rho) d^3r$ describes the behavior of the order parameter η near the second order phase transition and the coupling between the order parameter and the charge density reads:

$$\begin{aligned}
&\phi(\eta,\rho) = \phi_0 + \phi_\eta + \phi_{int} + \phi_e \qquad (1)\\
&\phi_\eta(\eta) = \frac{\alpha}{2}\eta^2 + \frac{\beta}{4}\eta^4 + \frac{\xi}{2}(\nabla\eta)^2 - \eta H\\
&\phi_{int}(\eta,\rho) = -\frac{\sigma}{2}\eta^2 \frac{\rho(\rho_0-\rho)}{\rho_0^2}\\
&\phi_e(\rho) = \frac{\gamma(\rho(r)-\bar{\rho})}{2\rho_0^2}\int \frac{(\rho(r')-\bar{\rho})}{|r-r'|} dV' + \frac{\vartheta(\rho(r)-\bar{\rho})^2}{2\rho_0^2}
\end{aligned}$$

where ϕ_0 is the density of the thermodynamic potential in the high-temperature phase, ϕ_η is the density of the thermodynamic potential of the low-temperature phase, α, β, ξ are coefficients in the expansion of the thermodynamic potentials in powers of the order parameter ($\alpha = \alpha^{'}(T - T_c)$, where T_c is critical temperature in the absence of doping, $\alpha^{'} = 1/C$, C is the Curie constant), ξ is proportional to the diffusion coefficient, and H is the external magnetic field. ϕ_{int} describes the interaction of the order parameter with the charge density, σ_0 is the constant of interactions. In order to provide global stability of the system we require $\sigma_0 > 0$ [12]. ϕ_e describes the charging effects due to Coulomb interaction between the charge carriers, and $\bar{\rho}$ is the average charge density. We assume that Coulomb contribution is the strongest: $\vartheta \ll a^2\gamma$. The effect of average dopant concentration $\bar{\rho}$ to the thermodynamic potential in the high-temperature phase is included in ϕ_0. The coefficient γ is inversely proportional to the static dielectric constant ε, $\gamma = \rho_0^2/\varepsilon$. As a result the coefficients in the thermodynamic potential depend on charge density ρ and the term $\sigma\rho(\rho_0 - \rho)$ determines the shift of the critical temperature T_c due to variation of the local charge density:

$$T_{c\rho}(x) = T_c + \frac{\sigma x(1-x)}{\alpha'} \tag{2}$$

Here $x = \rho/\rho_0$ and $\bar{x} = \bar{\rho}/\rho_0$ are dimensionless carrier densities. In the uniform case we have $x = \bar{x}$ ($\rho = \bar{\rho}$) and $\eta_u = H/2\tilde{\alpha}(\bar{x},T)$ for $T > T_c$ and $\eta_u = -\tilde{\alpha}(\bar{x},T)/\beta - H/\tilde{\alpha}(\bar{x},T)$ for $T < T_c$ ($\tilde{\alpha}(x,T) = \alpha(T) - \sigma x(1-x)$)

In the equilibrium state the order parameter and the carrier density are determined from equations: $\partial\phi(\eta,x)/\partial\eta = 0$, $\partial\phi(\eta,x)/\partial x = \mu_e$, μ_e is the chemical potential, which can be found from the conservation of the total number of carriers. The second equation determines the dependence of the charge density x_s on η ($\vartheta \ll a^2\gamma$):

$$\begin{aligned} x_s(\eta) \simeq \bar{x} \; &- \frac{\sigma(1-2\bar{x})}{8\pi\gamma}\Big(\nabla^2\eta^2 - \frac{\sigma}{4\pi\gamma}\nabla^2[\eta^2\nabla^2\eta^2]\Big) \\ &- \frac{\vartheta\sigma}{64\pi^2\gamma^2}\nabla^4\eta^2 \end{aligned} \tag{3}$$

Substituting Eq.(3) to Eq.(1) ($\vartheta \ll a^2\gamma$) we obtain the expression of the thermodynamic potential (1) $\phi_{\rho s}$ for the equilibrium distribution of the charge density $x_s(\eta)$:

$$\begin{aligned} \phi_{\rho s}(\eta) = \phi_\eta(\eta) - \frac{\sigma\bar{x}(1-\bar{x})}{2}\eta^2 - \frac{\sigma^2(1-2\bar{x})^2}{32\pi\gamma}(\nabla\eta^2)^2 \\ + \frac{\vartheta\sigma^2(1-2\bar{x})^2}{256\pi^2\gamma^2}(\nabla^2\eta^2)^2 + \frac{\sigma^3(1-2\bar{x})^2}{128\pi^2\gamma^2}\eta^2(\nabla^2\eta^2)^2. \end{aligned} \tag{4}$$

The negative sign in the third term of Eq.(4) indicates that the uniform state may be unstable towards inhomogeneous fluctuations.

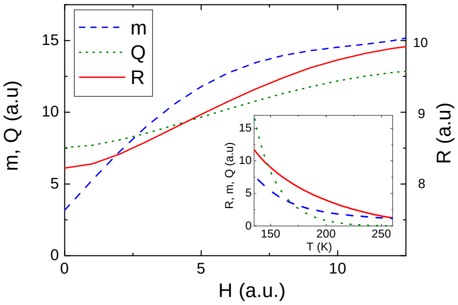

FIG. 1: Magnetic field dependence (temperature dependence in inset) of R_s, m and Q.

This instability leads to spatially inhomogeneous solutions. The most simple solution is spherically symmetric bubbles of the low symmetry phase separated by the large distance from each other. Thus this equilibrium inhomogeneous state in the low doped samples has the spherical form and the distribution of charge has a shape of electric double-layer [18]. This solution has characteristic size R_0. The characteristic average charge density inside of bubbles is x_1 and the average charge density outside of these regions is x_2. The average charge density in the system is $\bar{x}$. The average value of the order parameter inside of the bubble $\eta_1 \simeq \eta_0 + H/2(-\tilde{\alpha}(x_1,T))$ is relatively large, while the order parameter outside of bubbles is much smaller $\eta_2 = H/\tilde{\alpha}(x_2,T)$ where $\eta_0^2 = -\tilde{\alpha}(x_1,T)/\beta$. It is clear that the charge is concentrated near the surface of the sphere. Therefore we can apply the approximation of the double electrical layer for evaluation of the Coulomb energy. At large distances from the sphere the order parameter and the charge density are equal to their equilibrium values $x = \bar{x}$ and $\eta = \eta_s(\bar{x})$ ($\eta_s \simeq \eta_2(\bar{x}) = H/\tilde{\alpha}(\bar{x},T)$). Therefore the thermodynamic potential Φ_s of the volume V_0 in that case has the form:

$$\Phi_s(R_0,x_1) = \Phi_{s0} - \frac{A(x_1)}{3}R_0^3 + \frac{B(x_1)}{2}R_0^2 + \frac{C(x_1)}{4}R_0^4, \tag{5}$$

here $\Phi_{s0} = \phi_0 V_0 - H^2 V_0(2\tilde{\alpha}(x_2,T))^{-1}$, $A(x_1) = \pi\tilde{\alpha}^2(x_1,T)\beta^{-1} - 2\pi H^2\tilde{\alpha}^{-1}(x_2,T) + O(H^3)$, $B(x_1) \simeq 8\pi\xi d^{-1}\beta^{-1}(-\tilde{\alpha}(x_1,T) + H\eta_0^{-1}(x_1,T) + H^2(4\beta\eta_0^4(x_1,T))^{-1})$, $C(x_1) \simeq \gamma d(\bar{x} - x_1)^2 F$. Here we define dimensionless factor F ($F = 4\int \phi_e d^3r/\gamma R_0^4 d(\bar{x} - x_1)^2$) in order to parameterize the distribution of charge. $F = 1/18$ in the limit of the double electrical layer, V_0 is the volume per one bubble ($V_0 = V/n$ where n is the number of spheres), d is the interphase boundary thickness. Here we take into account the strong screening of the localized charges and write the energy in the double electrical layer approximation. In that case it is proportional to dR_0^4. If the screening is absent this energy is proportional to R_0^5 [7]. The parameters $A(x_1)$ and $B(x_1)$ (5) depend on temperature T and magnetic field H, and parameter $C(x_1)$ depends on the average charge density $\bar{x}$. Parameters $(\bar{x},T)$ are external and we find the phase diagram as a function of these parameters. Since $\bar{x}$ is determined by the doping, we describe the evolution of the properties of the system with doping.

The minimum of the potential $\Phi_s(R_0,x_1)$ (5) is determined by the set of equations: $\partial\Phi_s(R_0,x_1)/\partial R_0 = 0$ and $\partial\Phi_s(R_0,x_1)/\partial x_1 = 0$, which define the equilibrium values of parameters: R_s and x_{1s}. For the equilibrium size of the charged domain R_s we obtain:

$$R_s = \frac{y_\eta A_0(x_{1s}) - A(x_{1s})}{(y(x_{1s})^{-1}y_\eta - 1)C(x_{1s})} \tag{6}$$

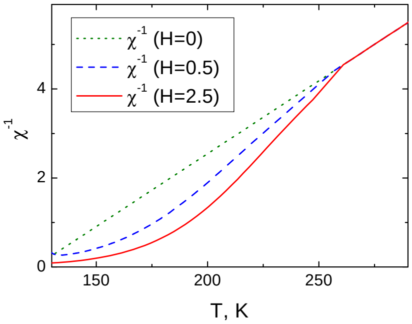

FIG. 2: The temperature dependence of $\chi^{-1}(T)$ for two different magnetic fields.

And x_{1s} is determined by the equation:

$$\frac{(y_\eta A_0(x_{1s})-A(x_{1s}))((y(x_{1s})A_0(x_{1s})-A(x_{1s})}{(y(x_{1s})^{-1}y_\eta-1)(y(x_{1s})y_\eta^{-1}-1)B(x_{1s})C(x_{1s})}=1 \tag{7}$$

where we use the notations: $\eta_3=\eta_0-H(-\tilde{\alpha}(x_1,T))^{-1}$, $A_0(x_1)=\pi\tilde{\alpha}^2(x_1,T)\beta^{-1}$, $y(x_1)=4\sigma(1-2x_1)(x_1-\bar{x})(-3\tilde{\alpha}(x_1,T))^{-1}$, $y_\eta=4\eta_1(3\eta_3)^{-1}$ For computer simulation we assume that $x_{2s}\simeq\bar{x}-\lambda(x_{1s}-\bar{x})$, where λ is ratio of the volume of the bubble (V_1) and the effective volume surrounding the bubble (V_2), where the charge density x differs from $\bar{x}$.

As a result for the charge of unite bubble Q we have:

$$Q(T,H)=\rho_0(x_1-\bar{x})\frac{4\pi}{3}R_s^3 \tag{8}$$

Average magnetization m is determined by equation:

$$m(T,H)=\eta_1\frac{4\pi}{3}\frac{R_s^3}{V_0}+\eta_2\left(1-\frac{4\pi}{3}\frac{R_s^3}{V_0}\right) \tag{9}$$

The temperature and magnetic field dependence of $R(T,H)$, $Q(T,H)$ and $m(T,H)$ are shown in Fig.1(a,b). Magnetic susceptibility $\chi(H,T)$ is temperature dependent ($\chi=dm(H)/dH$), as shown in the Fig.2.

Similarly we obtain the electric susceptibility:

$$\varepsilon_{eff}(T,H)=k\rho_0(x_1-\bar{x})\frac{4\pi}{3}R_s^3 \tag{10}$$

Here k is the coefficient which determines the local lattice deformation which appears due to charge localization and Jahn-Teller effect. Any charge displacement causes additional local deformation of the lattice and therefore protects against large charge displacements. As a result this local Jahn-Teller deformation may be estimated as $d_{JT}(r)\sim k_{JT}\rho_0(x(r)-\bar{x})$ ($k\sim k_{JT}^{-1}$) The effective dielectric constant $\varepsilon_{eff}(T,H)$ (10) is large because of large value of k. Importantly $\varepsilon_{eff}(T,H)$ depends on magnetic field, and therefore has magnetoelectric properties.

The condition that the inhomogeneous phase has lower energy then the uniform state ($\Phi_s(R_0,x_1)<\Phi_{unif}$) determine the region of the stability of the inhomogeneous phase. The equation $\Phi_s(R_s,x_1)=\phi_0V_0-H^2/2\tilde{\alpha}(\bar{x},T)$ define the upper boundary of the existence of the inhomogeneous state. As a result this formula and Eqs.(6,7) define the upper boundary $T_{s1}(\bar{x})$ in the recurrence form as a function of x_1:

$$T_{s1}=T_C+\frac{\sigma}{\alpha'}x_1(1-x_1)-\frac{\sigma Z}{\alpha'(1-2x_1)^2} \tag{11}$$

$$\bar{x}=x_1-\frac{2Z}{3(1-2x_1)^3},\quad \text{where } Z=\frac{16\beta\xi\gamma F}{\pi\sigma^3} \tag{12}$$

These equations determine the transition temperature T_{s1} to the stable inhomogeneous phase as a function of external parameters $\bar{x}$. This condition means that the energy of this inhomogeneous phase is lower then the energy of homogeneous state. Applying similar procedure we obtain the equation which defines the lower boundary of the inhomogeneous phase $T_{s2}(\bar{x})$. Note that lower boundary T_{s2} will be always close to the temperature $T_{c\rho}(\bar{x})$, because there is no any gain in energy, when the bubble of the high-temperature phase is formed ($\Phi_\eta(\eta=0)=0$, and $\Phi_\eta(\eta_0)<0$). It leads to the essential difference between the formation of the bubble of the low-temperature phase surrounded by the high-temperature phase and the bubble of the high-temperature phase surrounded by the low- temperature phase. The first one is energetically favorable and therefore the region of the existence of this bubbles is considerably large. It is important to note that Eqs.(10) which determine the phase diagram does not depend on d. This fact allows us to avoid optimization of the thermodynamic potential with respect to d. Typical phase diagram of the inhomogeneous state is presented in Fig.3. Phase transition to the nonhomogeneous state represents typical first order phase transition. Metastable inhomogeneous phase appears at the temperature T_{s0} which is much higher then the temperature of phase transition and it is shown in the phase diagram by dashed line. This line is determined by Eqs.(6,7) and $A(x_0)^2=4C(x_0,\bar{x})B(x_0,\bar{x})$.

In order to make the phase separation possible it is suf-

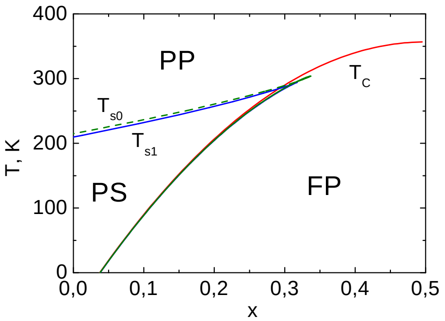

FIG. 3: Phase diagram of the system with $T_c=-60K$, $\sigma/\alpha'=1750K$, $Z=2\ 10^6$: PP is is the region of the stable high-temperature phase; FP is the region of the stable high-temperature phase with metastable bubbles of the low-temperature phase; PS is the region of the stable inhomogeneous phase and metastable homogeneous high-temperature phase.

ficient to have only small variation of the charge density per unite cell in comparison with average charge density $e(x_1 - \bar{x}) \simeq 0.1 - 0.2e$. We can estimate the Coulomb contribution to the free energy u_ρ as well as the energy gain due to formation of the low-temperature phase u_η (the forth and the second terms in Eq.(5)) per one unite cell. For the Coulomb contribution we obtain:

$$u_\rho = \Big(\frac{3e^2(x_1 - \bar{x})^2}{4\pi\varepsilon a}\Big)\frac{dR_0F}{a^2} \tag{13}$$

Substituting $\varepsilon = 30 - 40$ (the case of manganites), $F \simeq 1/18$, $R_0 \simeq 1 - 6nm(d \sim R_0)$, to Eq.(13) we obtain that u_ρ is less then $0.02eV$. The energy gain due to formation of the low-temperature phase is $u_\eta \simeq 3k_BT_c$ ($u_\eta \simeq a^3(\tilde{\alpha}(x_1, T = 0))^2/\beta \simeq a^3T_C\eta_0^2(x_1, T = 0)/C$, $C = \eta_0^2(T = 0)/3k_BN_A$, where N_A is the Avogadro number). Therefore $u_\eta \simeq 0.03 - 0.1eV > u_\rho$ and the phase separation becomes favorable. Therefore the typical length scale of the nano-regions may be estimated as $R_0 \simeq 1 - 5nm$.

The analysis of the pair distribution function obtained by neutron scattering shows that the charge density in manganites is localized on the scale of 3 to 4 interatomic distances[5, 19]. The extra charge in that case is not more then $0.1 - 0.2e$ per unite cell. This is consistent with our estimates. This state is characterized as the state with nano-dimensional charge and phase separation. Dynamics of these charged nano-regions may lead to high value of the effective dielectric constant $\varepsilon_{eff}(T, H)$ (10) in the low frequency range [20].

We have shown that the second order phase transition with strong dependence of critical temperature $T_{c\rho}(x)$ (2) on doping is unstable with respect to the formation of the spatially inhomogeneous charged states. Within the phenomenological Landau theory we have shown that these states appears at some temperature T_{s1}, which is substantially higher then the temperature $T_{c\rho}$ (Fig.3). As a result the phase transition becomes effectively first order phase transition. Note that the Coulomb interaction determines the charge distribution, the screening and the characteristic length scale of the nonhomogeneous states. The spatially inhomogeneous state becomes possible in the systems with the large dielectric constants and with relatively small charge density variations. We demonstrated that the effective dielectric constant $\varepsilon_{eff}(T, H)$ (10) is large and depends on magnetic field.

In conclusion we underline that the localized charged states and the phase separation appears even in the case of the second order phase transition. Properties of these states are described within the phenomenological theory of the phase transitions. The Coulomb interaction determines the spatial charge distribution, the screening and the characteristic length of charge localization. The inhomogeneous states become possible because of large dielectric constants and relatively small spatial variation of the charge density. Thise states in the low doped manganite may lead to the magnetoelectric behavior. The magnetocapacitance effect in the inhomogeneous state in low-doped systems may become the method of investigation of the inhomogeneous charge segregated states including low-doped cuprates near the threshold of the superconductivity.

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